RIE1 (Trion Phantom II) Processes

				Gas Flows (sccm)					
Name	**Pres (mT)**	**ICP**	**RIE**	**CF4**	**O2**	**SF6**	**CHF3**	**ER A/min**	**Comments**
CLEAN	250	500	200	5	98				typically run for 600sec
NITRIDE-icp1	150	350	25	45	5				non-resist mask, top layer
NITRIDE-icp2	150	350	25		5	45			Isotropic, high etch rate
NITRIDE-rie1	150		100	45	5				MOS type devices
OXIDE-icp1	150	350	25	45	5				non-resist mask, passivation, top layer
OXIDE-rie1	150		75	50				250	higher ER, resist mask
2x OXIDE-rie1	150		150	50				735	higher ER, resist mask
OXIDE-rie2	20		200		3		25	600	higher selectivity, resist mask
2x OXIDE-rie2	20		400		3		25	950	higher selectivity, resist mask
OXIDE-rie3	150		100	45	5			500	MOS type devices
2x OXIDE-rie3	150		200	45	5			1350	MOS type devices
POLYIMIDE	50	500	25		45		5	~5000	
RESIST	500	500	25		50				